ABSTRACT

SUBSTRATE PROCESSING METHOD

A substrate processing method capable of uniformly maintaining damage to a pattern structure under a thin film formed on a substrate includes supplying a source material to a substrate on which a pattern structure that is reactive with a reactant is formed; and supplying the reactant through at least a central gas inlet of a supply unit in a plasma atmosphere, wherein, during the supplying of the reactant, a blocking material different from the reactant is supplied through an additional gas inlet that is spaced apart from the central gas inlet of the supply unit, and a flow of the blocking material at the edge of the substrate is increased, thereby increasing a radical density of the reactant near a center of the substrate.

FIG. 1